

Silicon NPN Power Transistor

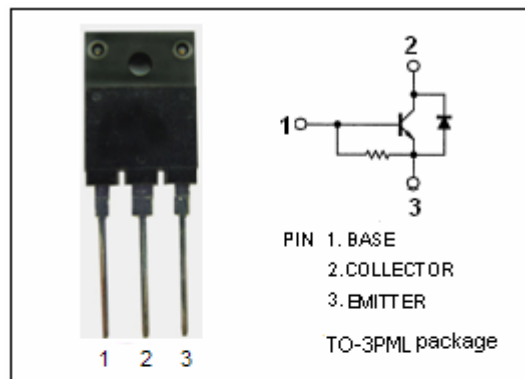
2SC4125

DESCRIPTION

- High Breakdown Voltage-
: $V_{CBO} = 1200V$ (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode

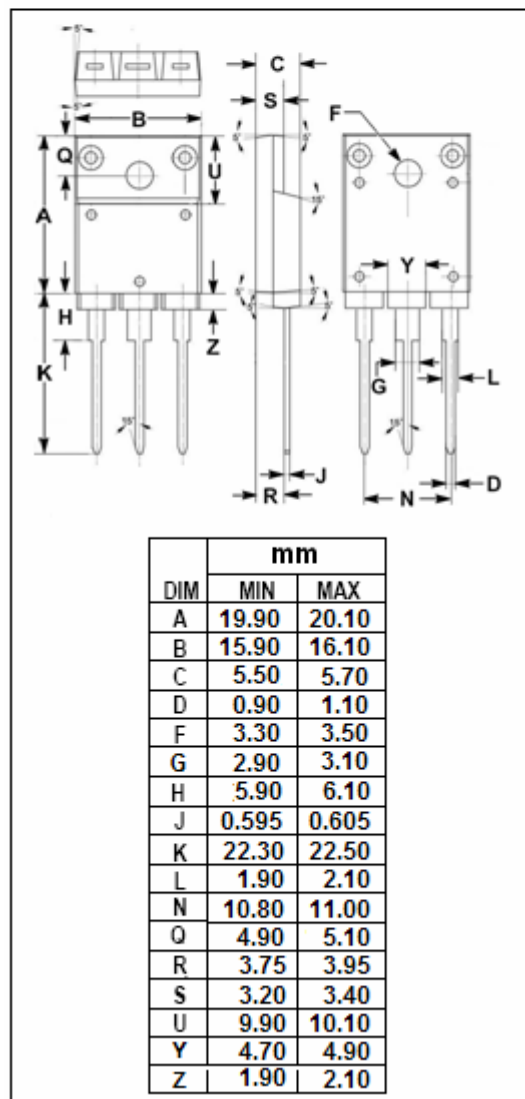
APPLICATIONS

- Designed for very high-definition color display horizontal deflection output applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	10	A
I_{CP}	Collector Current-Peak	25	A
P_C	Collector Power Dissipation @ $T_a=25$	3	W
	Collector Power Dissipation @ $T_c=25$	70	
T_J	Junction Temperature	150	
T_{stg}	Storage Temperature Range	-55~150	



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ELECTRICAL CHARACTERISTICS

 $T_C=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100mA; I_B=0$	800			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=8A; I_B=2A$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=8A; I_B=2A$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=800V; I_E=0$			10	μA
I_{CES}	Collector Cutoff Current	$V_{CE}=1200V; R_{BE}=0$			1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=4V; I_C=0$	40		130	mA
h_{FE-1}	DC Current Gain	$I_C=1A; V_{CE}=5V$	8			
h_{FE-2}	DC Current Gain	$I_C=8A; V_{CE}=5V$	4		6	
V_{ECF}	C-E Diode Forward Voltage	$I_F=10A$			2.0	V

Switching Times

t_s	Storage Time	$I_C=6A, I_{B1}=1.2A; I_{B2}=-2.4A$			3.0	μs
t_f	Fall Time			0.1	0.2	μs